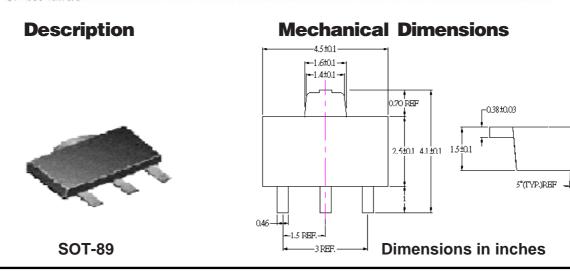


1.5 Amp Silicon **Controlled Rectifiers**



Feature:

- Driven directly with IC and MOS device.
- · Feature proprietary, void-free glass passivate · Designed for high volume, line-powered chips.
- Available in voltage ratings from 200 to 600 volts. (VDRM and VRRM)

• Sensitive gate trigger current.

control application in relay lamp drivers, small motor controls, gate drivers for large thyristors.

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS (Ta=25 C)

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CHARACTERISTICS	SYMBOL	PART NO	DATA	UNIT
Repetitive Peak Off-State Voltage and Repetitive Peak Reverse Voltage (1)	VDRM & VRRM	FCR150-6/8PA	400/600	VOLT
RMS On-State Current at Ta=57°C and Conduction Angle of 180°	I _T (RMS)		1.5	AMP
Peak Surge (Non-Repetitive)On-State Current, 2 Cycle ,at 50Hz or 60Hz	I _{TSM}		15	AMP
Peak Gate-Trigger Current for 3µ sec, Max	I _{GTM}		1.0	AMP
Peak Gate-Power Dissipation at IGT≤IGTM	P _{GM}		0.1	WATT
Average Gate-Power Dissipation	P _G (AV)		0.01	WATT
Peak gate reverse voltage	V _{RGM}		6	V
Peak Off-State Current, (1)Ta=25°C VDRM & VRRM=Max. Rating Ta=125°C	I _{drm} & I _{rrm}		10 100	μA MAX
Maximum On-State Voltage. (Peak) At Tc=25°C and IT =Rated Amps	V _{TM}		1.7	VOLT MAX
DC Holding Current,(1)	I _{HO}		5	mA MAX
Critical Rate-Of-Rise of off-State Voltage.(1) Gate Open,Ta=110°C	Critical dv/dt		35	V/μ sec
DC Gate –Trigger Current for Anode Voltage=7VDC, RL=100 Ω	I _{GT}		150	μA MAX
DC Gate –Trigger Voltage for Anode Voltage=7VDC, RL=100 Ω	V _{GT}		0.8	VOLT MAX
Gate-Controlled Turn-on Time tD+tR IGT=10mA	Tgt		2.2	µ sec
Thermal Resistance, Junction-to-Case	RθJ-C		75	°C/WATT TYP
Storage Temperature range	Tstg		-40 to + 150	°C
Operating Temperature Range, Tj	Toper		-40 to + 110	°C

(1)RGK=1K Ω



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